

NTE226 Germanium PNP Transistor Audio Power Amp

Description:

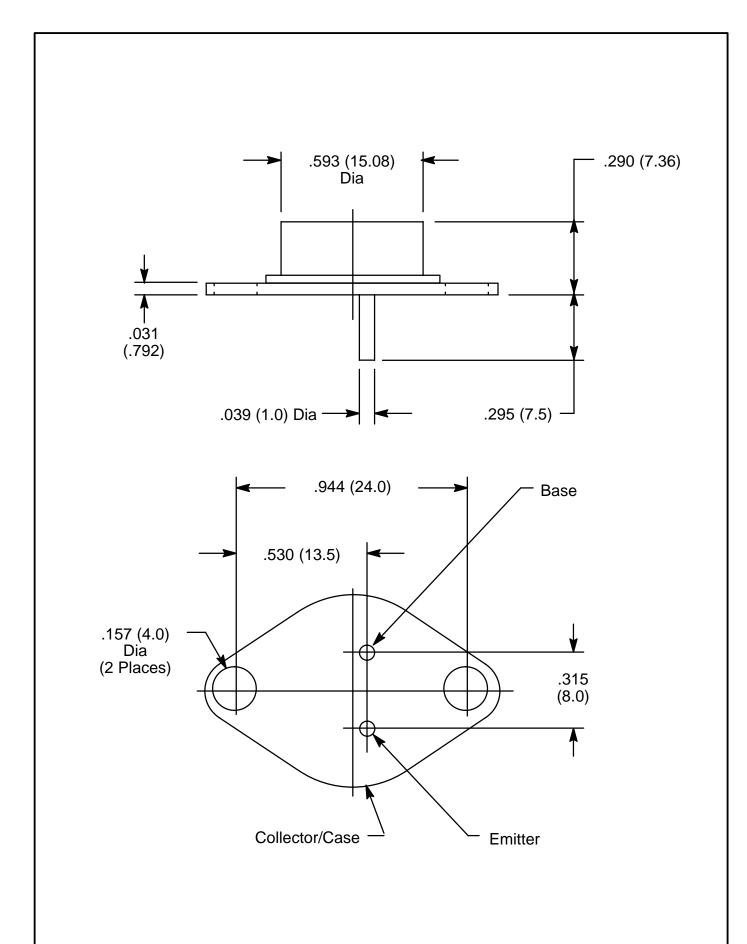
The NTE226 is a Germanium PNP transistor in a TO66 type package designed for high–fidelity, high–power output applications.

Absolute Maximum Ratings:

Collector–Base Voltage, V _{CBO}	35V
Collector–Emitter Voltage ($R_{BE} = 100\Omega$), V_{CER}	35V
Emitter–Base Voltage, V _{EBO}	6V
Collector Current, I _C	2A
Power Dissipation ($T_C = +25^{\circ}C$), P_C	12W
Operating Junction Temperature, T _J	+85°C
Storage Temperature Range, T _{stg} –55°	° to +85°C

<u>Electrical Characteristics:</u> $(T_A = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	$V_{CB} = 25V, I_{E} = 0$	_	_	200	μΑ
Emitter Cutoff Current	I _{EBO}	$V_{EB} = 6V, I_{C} = 0$	_	_	200	μΑ
DC Current Gain	h _{FE}	$V_{CE} = 1.5V, I_{C} = 200mA$	50	100	275	
Small-Signal Current Gain Resistance	f _{ob}	$V_{CE} = 1.5V, I_{C} = 200mA$	_	0.7	_	MHz
Base Spreading Resistance	r _{bb}	$V_{CE} = 1.5V$, $I_{C} = 200$ mA, $f = 6$ MHz	_	15	_	Ω



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